



HiPerDynFRED

 $V_{RRM} = 1200 V$ $I_{RM} = 2x = 25 A$

 $t_{rr} = 15 \, \text{ns}$

High Performance Dynamic Fast Recovery Diode Extreme Low Loss and Soft Recovery Parallel legs with series connected dice

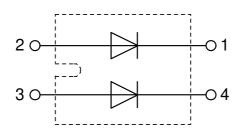
Part number

DSEP2x25-12C



Backside: isolated





Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low Irm-values
- Very soft recovery behaviour
- Soft reverse recovery for low EMI/RFI
- Low Irm reduces:
 - Power dissipation within the diode
 - Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package: SOT-227B (minibloc)

- Isolation Voltage: 3000 V~
- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Base plate: Copper internally DCB isolated
- Advanced power cycling

Disclaimer Notice

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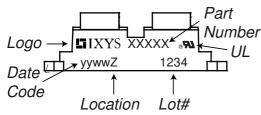


Fast Diode					Ratings		
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V _{RSM}	max. non-repetitive reverse blockir	ng voltage	$T_{VJ} = 25^{\circ}C$			1200	V
V _{RRM}	max. repetitive reverse blocking vo	oltage	$T_{VJ} = 25^{\circ}C$			1200	V
IR	reverse current, drain current	V _R = 1200 V	$T_{VJ} = 25^{\circ}C$			250	μΑ
		$V_R = 1200 V$	$T_{VJ} = 150$ °C			2	mΑ
V _F	forward voltage drop	I _F = 25 A	$T_{VJ} = 25^{\circ}C$			4.71	V
		$I_F = 50 \text{ A}$				5.92	٧
		I _F = 25 A	T _{VJ} = 150°C			2.95	V
		$I_F = 50 \text{ A}$				4.01	٧
I FAV	average forward current	T _C = 90°C	T _{VJ} = 150°C			25	Α
		rectangular d = 0.5					
V _{F0}	threshold voltage		$T_{VJ} = 150$ °C			1.95	V
\mathbf{r}_{F}	slope resistance	ss calculation only				40	mΩ
R _{thJC}	thermal resistance junction to case)				0.6	K/W
R _{thCH}	thermal resistance case to heatsin	k			0.1		K/W
P _{tot}	total power dissipation		$T_C = 25^{\circ}C$			210	W
I _{FSM}	max. forward surge current	$t = 10 \text{ ms}$; (50 Hz), sine; $V_R = 0 \text{ V}$	$T_{VJ} = 45^{\circ}C$			250	Α
CJ	junction capacitance	$V_R = 400 V f = 1 MHz$	$T_{VJ} = 25^{\circ}C$		18		pF
I _{RM}	max. reverse recovery current		$T_{VJ} = 25 ^{\circ}\text{C}$		5.5		Α
		$I_F = 30 \text{ A}; V_R = 600 \text{ V}$	$T_{VJ} = 100^{\circ}C$		12.5		Α
t _{rr}	reverse recovery time	$\begin{cases} I_F = 30 \text{ A; } V_R = 600 \text{ V} \\ -di_F / dt = 600 \text{ A/} \mu \text{s} \end{cases}$	$T_{VJ} = 25 ^{\circ}\text{C}$		15		ns
)		$T_{VJ} = 100^{\circ}C$		70		ns



Package SOT-227B (minibloc)				Ratings				
Symbol	Definition	Conditions			min.	typ.	max.	Unit
I _{RMS}	RMS current	per terminal					100	Α
T _{VJ}	virtual junction temperature	9			-40		150	°C
T _{op}	operation temperature			-40		125	°C	
T _{stg}	storage temperature			-40		150	°C	
Weight						30		g
M _D	mounting torque			1.1		1.5	Nm	
$\mathbf{M}_{_{T}}$	terminal torque			1.1		1.5	Nm	
d _{Spp/App}	creepage distance on surface striking distance through air		terminal to terminal	10.5	3.2			mm
d _{Spb/Apb}			terminal to backside	8.6	6.8			mm
V _{ISOL}	isolation voltage t = 1 second				3000			V
.002		t = 1 minute	50/60 Hz, RMS; I _{ISOL} ≤ 1 mA		2500			٧

Product Marking

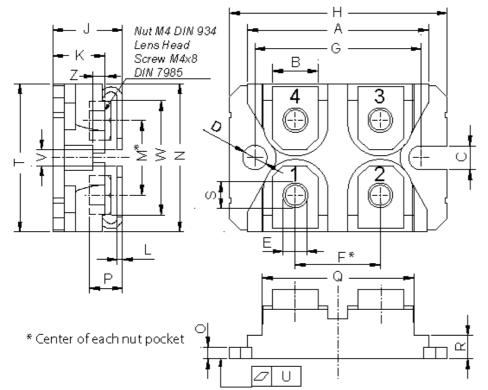


Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DSEP2x25-12C	DSEP2x25-12C	Tube	10	482021

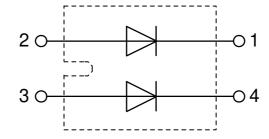
Equivalent Circuits for Simulation			* on die level	$T_{VJ} = 150^{\circ}C$
$I \rightarrow V_0$)—[R ₀]	Fast Diode		
V _{0 max}	threshold voltage	1.95		V
R _{0 max}	slope resistance *	36		mΩ



Outlines SOT-227B (minibloc)



Dim.	Millimeter		Inc	Inches	
DIIII.	min	max	min	max	
Α	31.50	31.88	1.240	1.255	
В	7.80	8.20	0.307	0.323	
С	4.09	4.29	0.161	0.169	
D	4.09	4.29	0.161	0.169	
Е	4.09	4.29	0.161	0.169	
F	14.91	15.11	0.587	0.595	
G	30.12	30.30	1.186	1.193	
Н	37.80	38.23	1.488	1.505	
J	11.68	12.22	0.460	0.481	
K	8.92	9.60	0.351	0.378	
L	0.74	0.84	0.029	0.033	
M	12.50	13.10	0.492	0.516	
N	25.15	25.42	0.990	1.001	
0	1.95	2.13	0.077	0.084	
Р	4.95	6.20	0.195	0.244	
Q	26.54	26.90	1.045	1.059	
R	3.94	4.42	0.155	0.167	
S	4.55	4.85	0.179	0.191	
Т	24.59	25.25	0.968	0.994	
U	-0.05	0.10	-0.002	0.004	
V	3.20	5.50	0.126	0.217	
W	19.81	21.08	0.780	0.830	
Ζ	2.50	2.70	0.098	0.106	





Fast Diode

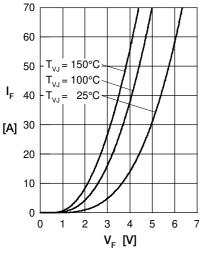


Fig. 1 Forward current I_F versus V_F

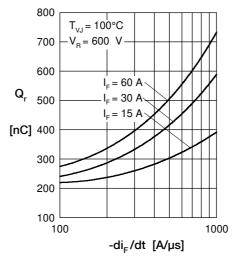


Fig. 2 Typ. reverse recov. charge Q_r versus $-di_F/dt$

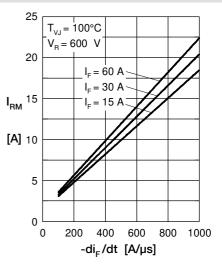


Fig. 3 Typ. peak reverse current $I_{\rm RM}$ versus $-{\rm di_F}/{\rm dt}$

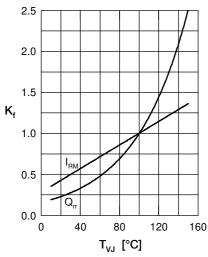


Fig. 4 Typ. dynamic parameters Q_r , I_{RM} versus T_{VJ}

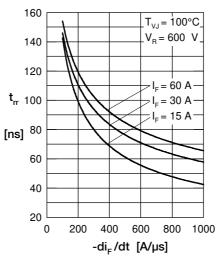


Fig. 5 Typ. recovery time t_{rr} versus $-di_{F}/dt$

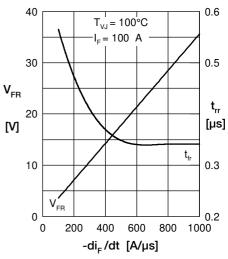


Fig. 6 Typ. peak forward voltage V_{FR} and t_{fr} versus di_{F}/dt

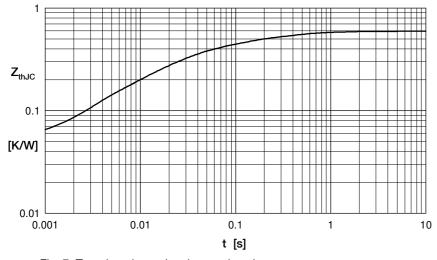


Fig. 7 Transient thermal resistance junction to case

Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t _i (s)
1	0.037	0.0002
2	0.07	0.0036
3	0.246	0.0235
4	0.176	0.142
5	0.07	0.7

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